TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1362

Low Frequency Power Amplifier Applications Power Switching Applications

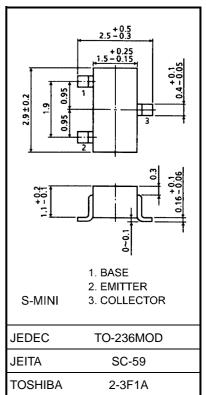
- High DC current gain: $h_{FE} = 120 \sim 400$
- Low saturation voltage: V_{CE} (sat) = -0.2 V (max)

 $(I_C = -400 \text{ mA}, I_B = -8 \text{ mA})$

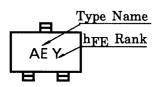
- Suitable for driver stage of small motor
- Small package

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-15	V
Collector-emitter voltage	V _{CEO}	-15	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-800	mA
Base current	Ι _Β	-160	mA
Collector power dissipation	P _C	200	mW
Junction temperature	Тj	150	°C
Storage temperature range	T _{stg}	-55~150	°C



Marking



Weight: 0.012 g (typ.)

Unit: mm

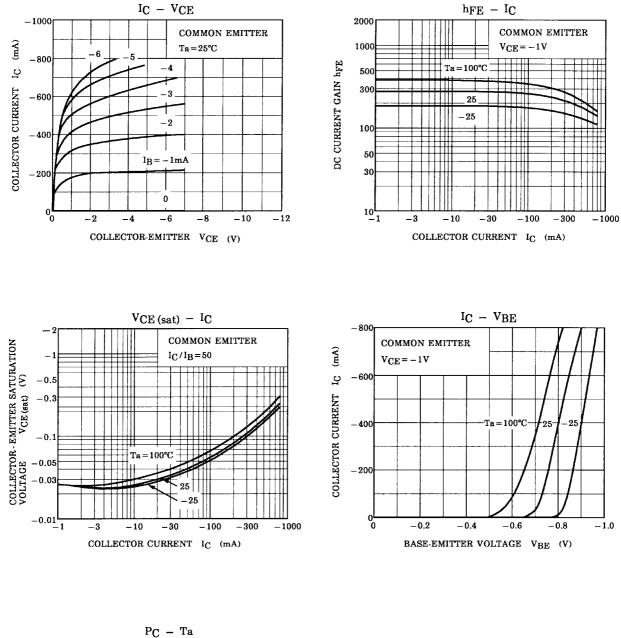
Electrical Characteristics (Ta = 25°C)

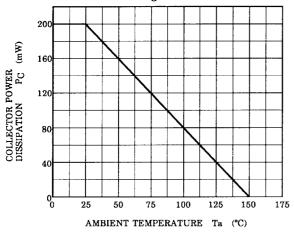
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -15 V, I_E = 0$	_	_	-100	nA
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, \text{ I}_{C} = 0$	_	_	-100	nA
Collector-emitter breakdown voltage	V (BR) CEO	$I_{C} = -10 \text{ mA}, I_{B} = 0$	-15	_	_	V
DC current gain	h _{FE (1)} (Note)	$V_{CE} = -1 V, I_C = -100 mA$	120	_	400	
	h _{FE (2)}	$V_{CE} = -1 \text{ V}, I_{C} = -800 \text{ mA}$	40	_		
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = -400 \text{ mA}, I_{B} = -8 \text{ mA}$	_	_	-0.2	V
Base-emitter voltage	V _{BE}	$V_{CE} = -1 V, I_{C} = -10 mA$	-0.5	_	-0.8	V
Transition frequency	fT	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$	_	120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	13	—	pF

Note: $h_{FE(1)}$ classification Y (Y): 120~240, GR (G): 200~400

() marking symbol

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